

WHAT IS CLAIMED IS:

1. A method of forming a bump, comprising:

providing a wafer having a plurality of chips, wherein each of the chips is provided

with a plurality of bonding pads thereon;

5 performing a wet etching using hydrogen peroxide or hydrogen fluoride;

forming an under ball metallurgy (UBM) layer on each of the bonding pads; and

forming a bump on the UBM layer.

2. The method of claim 1, wherein the material used to form the bonding pad is

aluminum.

10 3. The method of claim 1, wherein the material used to form the bump is gold.

4. The method of claim 1, further performing a dry etching process to remove a native

oxide layer, if any, on the bonding pad before the UBM layer is formed.

5. The method of claim 1, wherein the bump is formed by plating.

6. A method of forming a bump, comprising:

15 providing a wafer having a plurality of chips, wherein each of the chips is provided

with a plurality of bonding pads;

performing a wet etching using a peroxide;

forming an under ball metallurgy (UBM) layer on each of the bonding pads; and

forming a bump on the UBM layer.

7. The method of claim 6, wherein the material used to form the bonding pad is

aluminum.

8. The method of claim 6, wherein the material used to form the bump is gold.

5 9. The method of claim 6, further performing a dry etching process to remove a native
oxide layer, if any, on the bonding pad before the UBM layer is formed.

10. The method of claim 6, wherein the bump is formed by plating.

11. The method of claim 6, wherein the peroxide is hydrogen peroxide.